

Document Title**32K x8 bit 3.3V Low Power CMOS slow SRAM**Revision History

<u>Revision No</u>	<u>History</u>	<u>Draft Date</u>	<u>Remark</u>
00	Revision History Insert Revised - Datasheet format change - PDIP package type insert - Pin configuration change	Jul.08.2000	Final
01	Marking Information Add Revised - AC Test Condition Add : 5pF Test Load	Dec.04.2000	Final
02	Changed Logo - HYUNDAI - > hynix	Apr.30.2000	Final

DESCRIPTION

The GM76V256C is a high-speed, low power and 32,786 X 8-bits CMOS Static Random Access Memory fabricated using Hynix's high performance CMOS process technology. It is suitable for use in low voltage operation and battery back-up application. This device has a data retention mode that guarantees data to remain valid at the minimum power supply voltage of 2.0 volt.

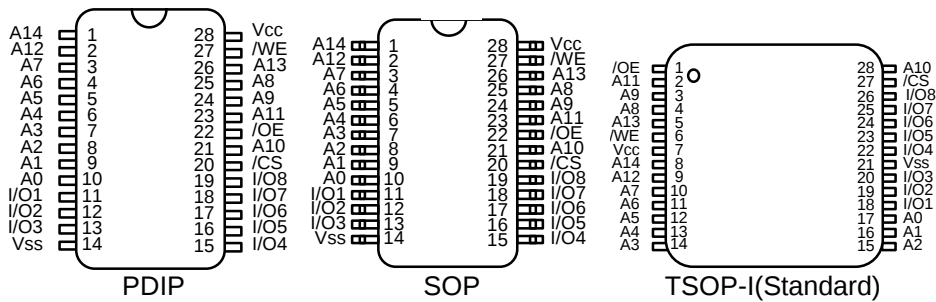
FEATURES

- Fully static operation and Tri-state output
- TTL compatible inputs and outputs
- Low power consumption
- Battery backup(L/LL-part)
 - 2.0V(min.) data retention
- Standard pin configuration
 - 28 pin 600mil PDIP
 - 28 pin 330mil SOP
 - 28 pin 8x13.4 mm TSOP-I
 (Standard)

Product No.	Voltage (V)	Speed (ns)	Operation Current(mA)	Standby Current(uA)		Temperature (°C)
				L	LL	
GM76V256C	3.3	85/100	2	20	10	0~70(Normal)
GM76V256CE	3.3	85/100	2	30	15	-25~85(Extended)

Note 1. Current value is max.

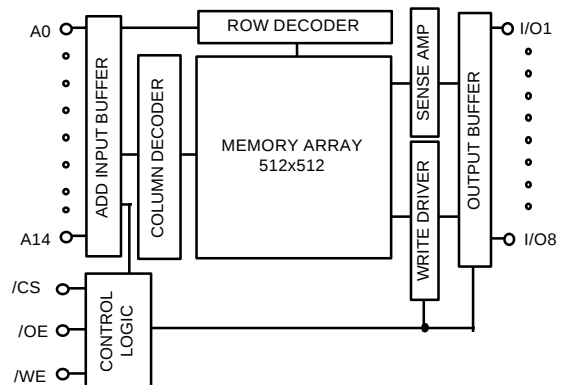
PIN CONNECTION



PIN DESCRIPTION

Pin Name	Pin Function
/CS	Chip Select
/WE	Write Enable
/OE	Output Enable
A0 ~ A14	Address Inputs
I/O1 ~ I/O8	Data Input/Output
Vcc	Power
Vss	Ground

BLOCK DIAGRAM



ORDERING INFORMATION

Part No.	Speed	Power	Temp	Package
GM76V256CL	85/100	L-part	0 to 70°C	PDIP
GM76V256CLL	85/100	LL-part	0 to 70°C	PDIP
GM76V256CLE	85/100	L-part	-25 to 85°C	PDIP
GM76V256CLLE	85/100	LL-part	-25 to 85°C	PDIP
GM76V256CLFW	85/100	L-part	0 to 70°C	SOP
GM76V256CLLFW	85/100	LL-part	0 to 70°C	SOP
GM76V256CLEFW	85/100	L-part	-25 to 85°C	SOP
GM76V256CLLEFW	85/100	LL-part	-25 to 85°C	SOP
GM76V256CLT	85/100	L-part	0 to 70°C	TSOP-I Standard
GM76V256CLLT	85/100	LL-part	0 to 70°C	TSOP-I Standard
GM76V256CLET	85/100	L-part	-25 to 85°C	TSOP-I Standard
GM76V256CLLET	85/100	LL-part	-25 to 85°C	TSOP-I Standard

ABSOLUTE MAXIMUM RATING (1)

Symbol	Parameter	Rating	Unit
V _{CC} , V _{IN} , V _{OUT}	Power Supply, Input/Output Voltage	-0.3 to 4.6	V
T _A	Operating Temperature	GM76V256C	0 to 70
		GM76V256CE	-25 to 85
T _{STG}	Storage Temperature	-65 to 150	°C
P _D	Power Dissipation	1.0	W
I _{OUT}	Data Output Current	50	mA
T _{SOLDER}	Lead Soldering Temperature & Time	260 •10	°C•sec

Note

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is stress rating only and the functional operation of the device under these or any other conditions above those indicated in the operation of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

Symbol	Parameter	Min.	Typ.	Max.	Unit
V _{CC}	Power Supply Voltage	3.0	3.3	3.6	V
V _{SS}	Ground	0	0	0	V
V _{IH}	Input High Voltage	2.2	-	V _{CC} +0.3	V
V _{IL}	Input Low Voltage	-0.3(1)	-	0.4	V

Note

- V_{IL} = -3.0V for pulse width less than 50ns

TRUTH TABLE

/CS	/WE	/OE	Mode	I/O Operation
H	X	X	Standby	High-Z
L	H	H	Output Disabled	High-Z
L	H	L	Read	Data Out
L	L	X	Write	Data In

Note

- H=V_{IH}, L=V_{IL}, X=Don't Care

DC CHARACTERISTICS

$V_{CC} = 3.3V \pm 10\%$, $T_A = 0^\circ C$ to $70^\circ C$ (Normal)/ $-25^\circ C$ to $85^\circ C$ (Extended), unless otherwise specified.

Symbol	Parameter	Test Condition		Min.	Typ.	Max.	Unit
ILI	Input Leakage Current	$V_{SS} \leq V_{IN} \leq V_{CC}$		-1	-	1	uA
ILO	Output Leakage Current	$V_{SS} \leq V_{OUT} \leq V_{CC}$, /CS = VIH or /OE = VIH or /WE = VIL		-1	-	1	uA
Icc	Operating Power Supply Current	/CS = VIL, VIN = VIH or VIL, II/O = 0mA		-	-	2	mA
ICC1	Average Operating Current	/CS = VIL, VIN = VIH or VIL Min. Duty Cycle = 100%, II/O = 0mA		-	-	35	mA
ICC2	Average Operating Current	/CS = VIL, VIN = VIH or VIL Cycle = 1us , II/O = 0mA		-	-	5	mA
ISB	TTL Standby Current (TTL Inputs)	/CS= VIH, VIN = VIH or VIL		-	-	0.5	mA
ISB1	CMOS Standby Current (CMOS Inputs)	$/CS \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq V_{SS} + 0.2V$	L	-	-	20	uA
			LL	-	-	10	uA
			LE	-	-	30	uA
			LLE	-	-	15	uA
VOL	Output Low Voltage	IOL = 2.1mA		-	-	0.4	V
VOH	Output High Voltage	IOH = -1.0mA		2.4	-	-	V

Note : Typical values are at $V_{CC} = 3.3V$, $T_A = 25^\circ C$

AC CHARACTERISTICS(I)

$V_{CC} = 3.3V \pm 10\%$, $T_A = 0^\circ C$ to $70^\circ C$ (Normal) / $-25^\circ C$ to $85^\circ C$ (Extended) unless otherwise specified.

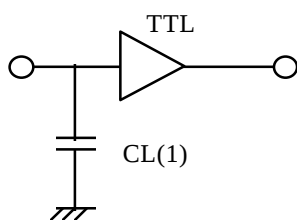
#	Symbol	Parameter	-85		-10		Unit
			Min.	Max.	Min	Max.	
READ CYCLE							
1	tRC	Read Cycle Time	85	-	100	-	ns
2	tAA	Address Access Time	-	85	-	100	ns
3	tACS	Chip Select Access Time	-	85	-	100	ns
4	tOE	Output Enable to Output Valid	-	45	-	50	ns
5	tCLZ	Chip Select to Output in Low Z	10	-	10	-	ns
6	tOLZ	Output Enable to Output in Low Z	5	-	5	-	ns
7	tCHZ	Chip Disable to Output in High Z	0	30	0	35	ns
8	tOHZ	Out Disable to Output in High Z	0	30	0	35	ns
9	tOH	Output Hold from Address Change	10	-	15	-	ns
WRITE CYCLE							
10	tWC	Write Cycle Time	85	-	100	-	ns
11	tCW	Chip Selection to End of Write	75	-	80	-	ns
12	tAW	Address Valid to End of Write	70	-	80	-	ns
13	tAS	Address Set-up Time	0	-	0	-	ns
14	tWP	Write Pulse Width	60	-	70	-	ns
15	tWR	Write Recovery Time	0	-	0	-	ns
16	tWHZ	Write to Output in High Z	0	30	0	30	ns
17	tDW	Data to Write Time Overlap	35	-	40	-	ns
18	tDH	Data Hold from Write Time	0	-	0	-	ns
19	tOW	Output Active from End of Write	5	-	10	-	ns

AC TEST CONDITIONS

$T_A = 0^{\circ}\text{C}$ to 70°C (Normal) / -25°C to 85°C (Extended) unless otherwise specified.

Parameter		Value
Input Pulse Level		0.4V to 2.2V
Input Rise and Fall Time		5ns
Input and Output Timing Reference Level		1.5V
Output Load	tCLZ,tOLZ,tCHZ,tOHZ,tWHZ,tOW	CL = 5pF + 1TTL Load
	Others	CL = 100pF + 1TTL Load

AC TEST LOADS



Note : Including jig and scope capacitance

CAPACITANCE

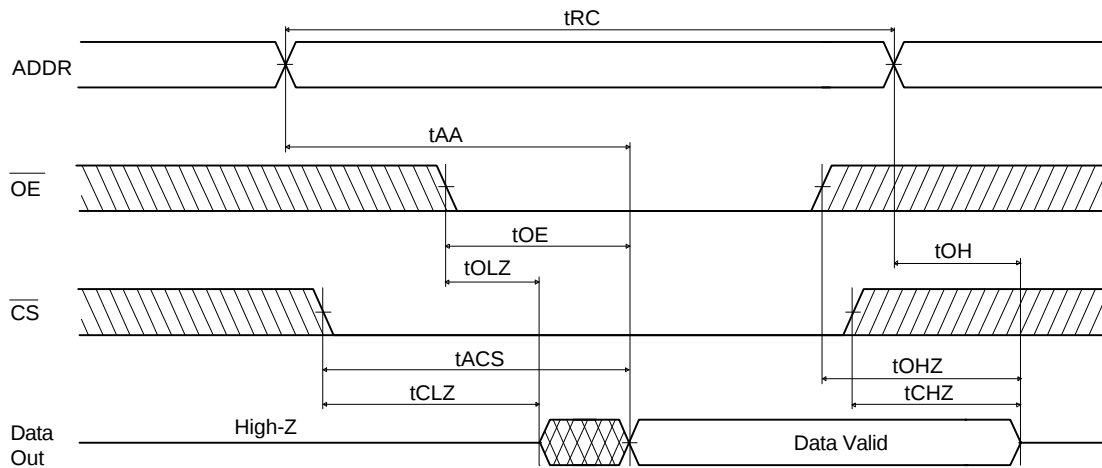
$T_A = 25^{\circ}\text{C}$, $f = 1.0\text{MHz}$

Symbol	Parameter	Condition	Max.	Unit
C_{IN}	Input Capacitance	$V_{IN} = 0\text{V}$	6	pF
$C_{I/O}$	Input /Output Capacitance	$V_{I/O} = 0\text{V}$	8	pF

Note : These parameters are sampled and not 100% tested

TIMING DIAGRAM

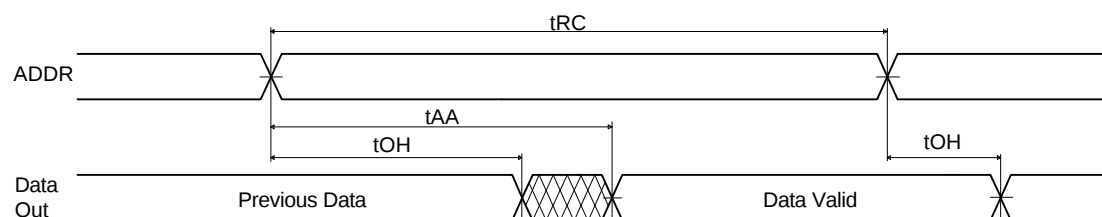
READ CYCLE 1



Note(READ CYCLE):

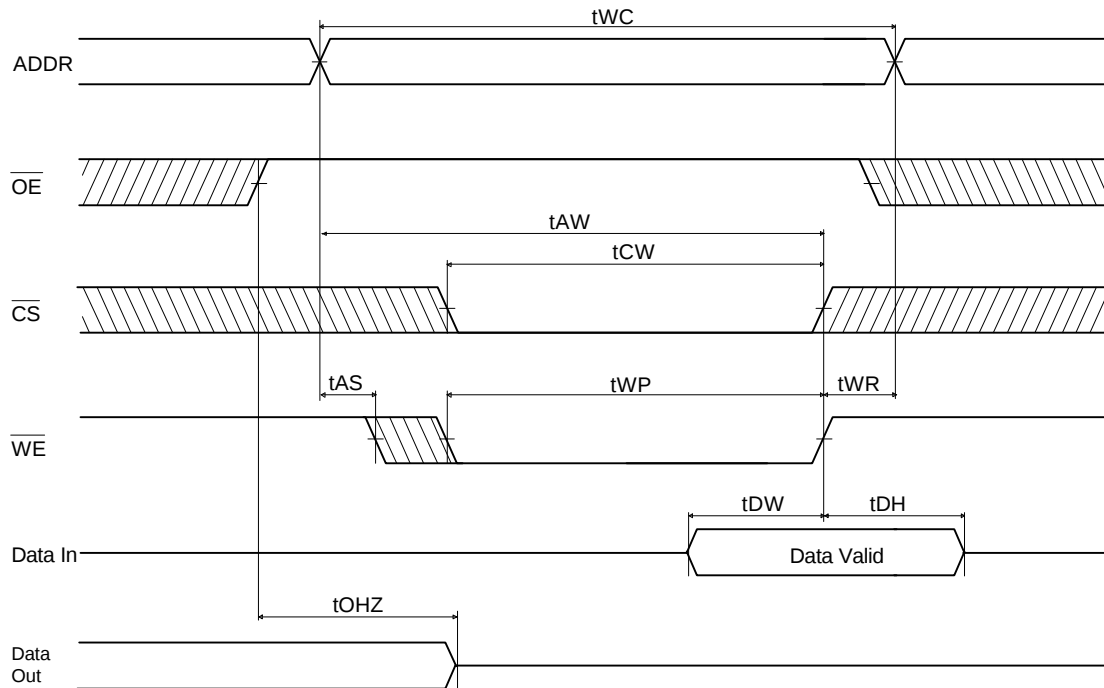
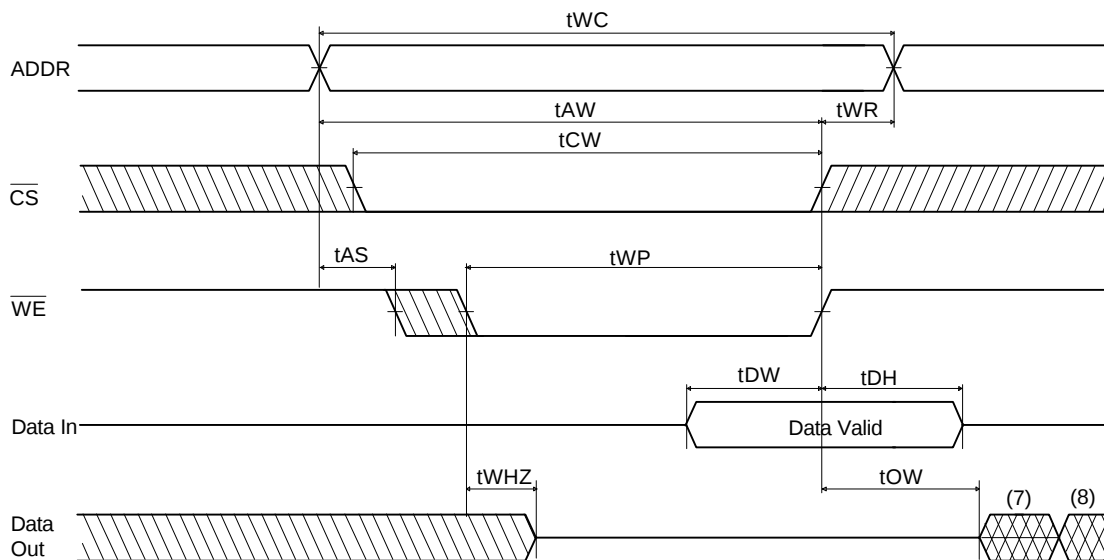
1. t_{CHZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, t_{CHZ} max. is less than t_{CLZ} min. both for a given device and from device to device.
3. $/WE$ is high for the read cycle.

READ CYCLE 2



Note(READ CYCLE):

1. $/WE$ is high for the read cycle.
2. Device is continuously selected $/CS = V_{IL}$.
3. $/OE = V_{IL}$.

WRITE CYCLE 1 (/OE Clocked)

WRITE CYCLE 2 (/OE Low Fixed)


Notes(WRITE CYCLE):

1. A write occurs during the overlap of a low /CS and a low /WE. A write begins at the latest transition among /CS going low and /WE going low: A write ends at the earliest transition among /CS going high and /WE going high. t_{WP} is measured from the beginning of write to the end of write.
2. t_{cw} is measured from the later of /CS going low to the end of write .
3. t_{as} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change. t_{WR} is applied in case a write ends as /CS, or /WE going high.
5. If /OE and /WE are in the read mode during this period, and the I/O pins are in the output low-Z state, input of opposite phase of the output must not be applied because bus contention can occur.
6. If /CS goes low simultaneously with /WE going low, or after /WE going low, the outputs remain in high impedance state.
7. DOUT is the same phase of the latest written data in this write cycle.
8. DOUT is the read data of the new address.

DATA RETENTION CHARACTERISTIC

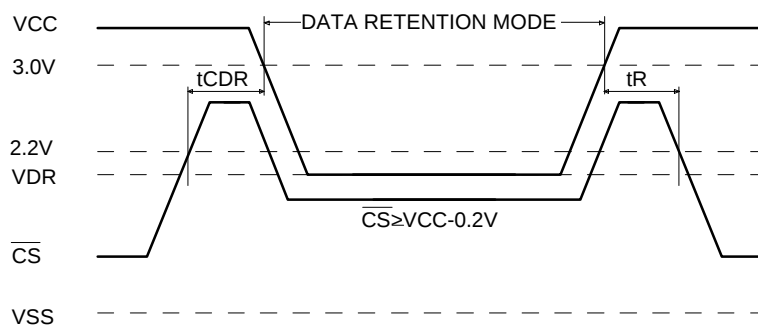
TA=0°C to 70°C (Normal)

Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
VDR	Vcc for Data Retention	$CS \geq V_{CC}-0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq V_{SS} + 0.2V$	2.0	-	-	V
ICCDR	Data Retention Current	$V_{CC} = 3.0V$, $/CS \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq V_{SS} + 0.2V$	L	1	15	uA
			LL	0.5	7	uA
			LE	1	20	uA
			LLE	0.5	10	uA
tCDR	Chip Deselect to Data Retention Time	See Data Retention	0	-	-	ns
tR	Operating Recovery Time	Timing Diagram	tRC(2)	-	-	ns

Notes

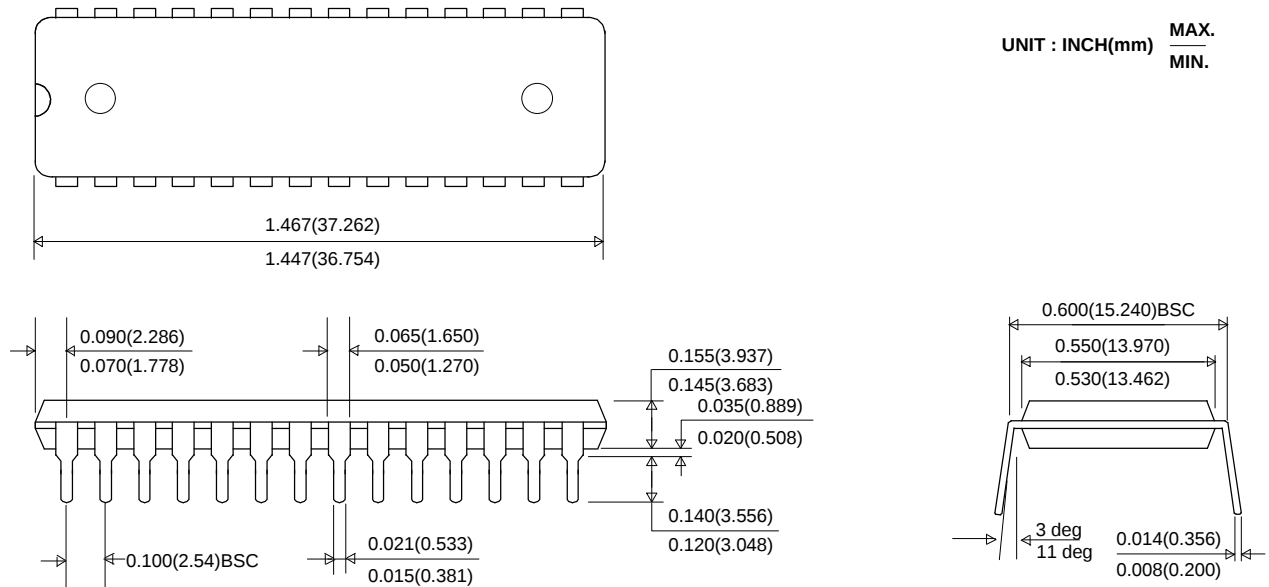
1. Typical values are under the condition of TA = 25°C.
2. tRC is read cycle time.

DATA RETENTION TIMING DIAGRAM

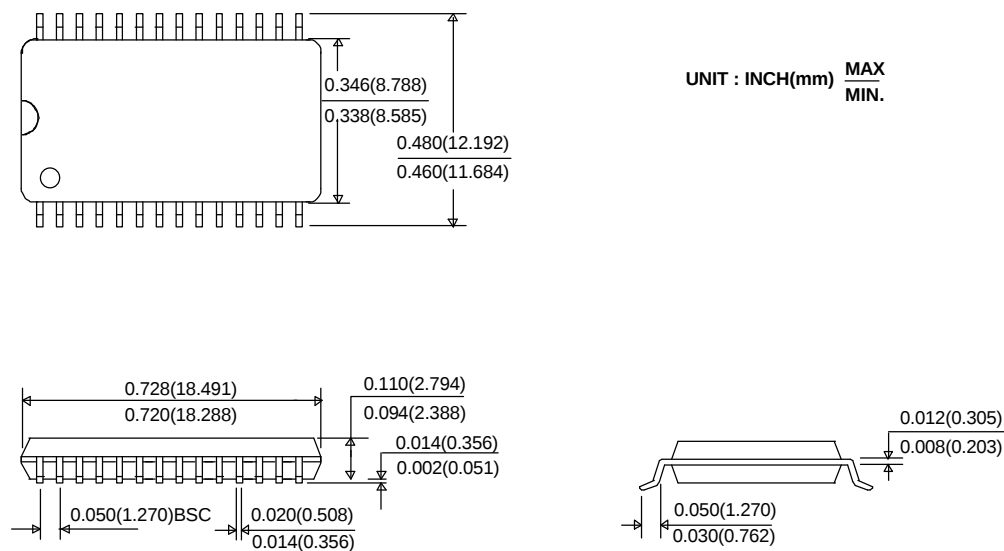


PACKAGE INFORMATION

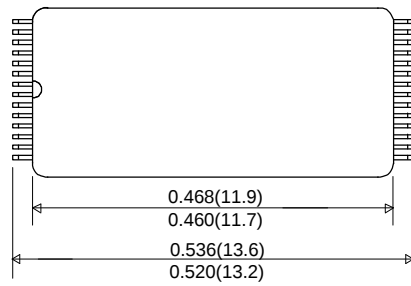
28pin 600mil Dual In-Line Package(Blank)



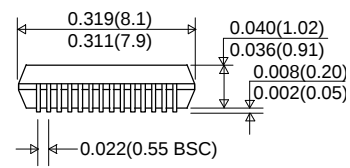
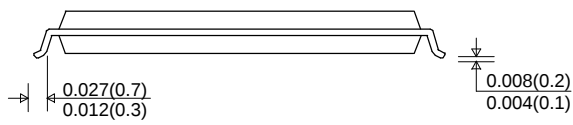
28pin 330mil Small Outline Package(FW)



28pin 8x13.4mm Thin Small Outline Package Standard(T)



UNIT : INCH(mm) $\frac{\text{MAX.}}{\text{MIN.}}$



MARKING INFORMATION

Package	Marking Example
PDIP	H Y U N D A I G M 7 6 V 2 5 6 C c c - s s t y y w w K O R E A
SOP	H Y U N D A I G M 7 6 V 2 5 6 C c c F W s s t y y w w K O R E A
TSOP-I	H Y U N D A I G M 7 6 V 2 5 6 C c c T s s t y y w w K O R E A
Index	
• HYUNDAI • KOREA • GM76V256C • cc • Blank / FW / T • ss • t • yy • ww	: Hynix Logo : Origin Country : Part Name : Power Consumption - L : Low Power - LL : Low Low Power : Package Type - Blank : DIP - FW : SOP - T : TSOP-I : Speed - 85 : 85ns - 10 : 100ns : Temperature - Blank : Commercial (0 ~ 70 °C) - E : Extended (-25 ~ 85 °C) : Year (ex : 00 = year 2000, 01 = year 2001) : Work Week (ex : 12 = ww12) Note - Capital Letter : Fixed Item - Small Letter : Non-fixed Item